Amendments to the Claims

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims

1-14. (Cancelled).

15. (Currently amended) A method for producing a flexible thin film capacitor comprising:

forming a metal oxide adhesive film on a substrate formed of at least one selected from the group consisting of an organic polymer and a metal foil, wherein the metal oxide adhesive film comprises at least one metal selected from Cr, NiCr, Ti, Co, Ge, Cu, Sn, Mo and W, and

forming a first metal electrode film, an inorganic high dielectric film and a second metal electrode film in this order on the metal oxide adhesive film, using respective masks;

wherein the first metal electrode film, the inorganic high dielectric film and the second metal dielectric film are formed in contact with the metal oxide adhesive film, thereby being integrated with the substrate by the metal oxide adhesive film,

wherein when the substrate comprises an organic polymer, the method further comprises

forming a peeling film on a base formed of at least one selected from the group consisting of an inorganic material and a metal material, wherein the peeling film is formed of at least one material selected from the group consisting of SiO_2, Si_3N_4 and coating glass;

applying an organic polymer material onto the peeling film; and

curing the organic polymer material by a heat treatment or light irradiation, thereby forming the substrate formed of an organic polymer on the peeling film.

16. (Cancelled)

17. (Previously presented) The method for producing a flexible thin film capacitor according to claim 15, wherein a metal adhesive film is formed in a region where the first metal electrode film is to be formed on the metal oxide adhesive film.

18. (Original) The method for producing a flexible thin film capacitor according to claim 15, wherein the metal electrode film is formed by at least one method selected from the group consisting of DC magnetron sputtering, RF magnetron sputtering, ECR magnetron sputtering, a CVD method and a vacuum evaporation method.

19. (Original) The method for producing a flexible thin film capacitor according to claim 15, wherein the inorganic high dielectric film is formed by at least one method selected from the group consisting of RF magnetron sputtering, ECR magnetron sputtering, a CVD method and a sol-gel process.

20. (Original) The method for producing a flexible thin film capacitor according to claim 15, wherein the inorganic high dielectric film is formed at a temperature up to 300°C.

21. (Original) The method for producing a flexible thin film capacitor according to claim 15, wherein the inorganic high dielectric film is formed at a deposition rate of not less than 10nm/min.

22. (Previously presented) The method for producing a flexible thin film capacitor according to claim 15, wherein the metal oxide adhesive film is formed by at least one method selected from the group consisting of RF magnetron sputtering, ECR magnetron sputtering, a vacuum evaporation method, a CVD method and a sol-gel process.

23. (Previously presented) The method for producing a flexible thin film capacitor according to claim 15, wherein the metal oxide adhesive film is formed by treating a metal film with a solution, and the metal film is formed by at least one method selected from the group consisting of DC magnetron sputtering, RF magnetron sputtering, ECR magnetron sputtering, a CVD method and a vacuum evaporation method.

24. (Original) The method for producing a flexible thin film capacitor according to claim 23, wherein the solution is at least one selected from the group consisting of concentrated nitric acid, phosphoric acid, chloric acid and perchloric acid.

25-26. (Cancelled)

27. (Currently amended) The method for producing a flexible thin film capacitor according to claim 15 ~~26~~, wherein the organic polymer material is at least one liquid substance selected from the group consisting of thermosetting or photocurable polyimide, polyamide, polyimide-amide, polyester, epoxy resin, polyurethane, epoxy acrylate and polyacrylic ester.

28. (Currently amended) The method for producing a flexible thin film capacitor according to claim 15 ~~26~~, wherein the peeling film is formed by at least one method selected from the group consisting of a vacuum evaporation method, sputtering, a CVD method and a sol-gel process.

29. (Cancelled)

30. (Currently amended) The method for producing a flexible thin film capacitor according to claim 15 ~~26~~, further comprising peeling the organic polymer substrate from the base by using a liquid or gas peeling solvent.

31. (Original) The method for producing a flexible thin film capacitor according to claim 30, wherein at least one liquid solvent selected from the group consisting of hydrofluoric acid, sodium hydrofluorate, and concentrated phosphoric acid is used as the peeling solvent.

32. (Original) The method for producing a flexible thin film capacitor according to claim 30, wherein a gas containing at least one gas selected from the group consisting of CF_4 and CHF_3 is used as the peeling solvent.

33. (Original) The method for producing a flexible thin film capacitor according to claim 30, wherein a mixed gas containing CF_4 and H_2 is used as the peeling solvent.

34. (Original) The method for producing a flexible thin film capacitor according to claim 15, further comprising forming a protective film on the first metal electrode film, the inorganic high dielectric film and the second electrode film.

35. (Original) The method for producing a flexible thin film capacitor according to claim 34, wherein the protective film is formed by at least one method selected from the group consisting of a vacuum evaporation method, puttering, a CVD method, a sol-gel process, screen printing and coating with a dispenser.

36. (Canceled)